Amplifier Transistors

PNP Silicon

Features

• Pb-Free Packages are Available*



Rating	Symbol	Value	Unit		
Collector – Emitter Voltage	V _{CEO}	-45	Vdc		
Collector – Base Voltage	V _{CBO}	-50	Vdc		
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc		
Collector Current – Continuous	Ic	-100	mAdc		
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.8	mW mW/°C		
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C		
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C		

THERMAL CHARACTERISTICS

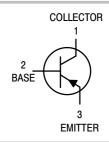
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



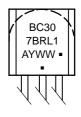
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MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC307BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = -2.0 mAdc, I _B = 0)	V _{(BR)CEO}	-45	_	-	Vdc
Emitter – Base Breakdown Voltage $(I_E = -100 \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	-	-	Vdc
Collector–Emitter Leakage Current $(V_{CES} = -50 \text{ V}, V_{BE} = 0)$ $(V_{CES} = -50 \text{ V}, V_{BE} = 0) \text{ T}_A = 125^{\circ}\text{C}$	I _{CES}	- -	-0.2 -0.2	-15 -4.0	nAdc μA
ON CHARACTERISTICS			•		
DC Current Gain	h _{FE}	_ 200 _	150 290 180	- 460 -	_
Collector – Emitter Saturation Voltage $ \begin{pmatrix} I_C = -10 \text{ mAdc, } I_B = -0.5 \text{ mAdc} \\ I_C = -10 \text{ mAdc, } I_B = \text{see Note 1} \\ I_C = -100 \text{ mAdc, } I_B = -5.0 \text{ mAdc} \end{pmatrix} $	V _{CE} (sat)	- - -	-0.10 -0.30 -0.25	-0.3 -0.6 -	Vdc
Base – Emitter Saturation Voltage $ \begin{array}{l} (I_C = -10 \text{ mAdc}, I_B = -0.5 \text{ mAdc}) \\ (I_C = -100 \text{ mAdc}, I_B = -5.0 \text{ mAdc}) \end{array} $	V _{BE(sat)}	- -	-0.7 -1.0	- -	Vdc
Base–Emitter On Voltage ($I_C = -2.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}$)	V _{BE(on)}	-0.55	-0.62	-0.7	Vdc
DYNAMIC CHARACTERISTICS					
Current – Gain – Bandwidth Product $(I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz})$	f⊤	_	280	_	MHz
Common Base Capacitance (V _{CB} = -10 Vdc, I _C = 0, f = 1.0 MHz)	C _{cbo}	_	-	6.0	pF
Noise Figure (I _C = -0.2 mAdc, V _{CE} = -5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz)	NF	-	2.0	10	dB

TYPICAL CHARACTERISTICS

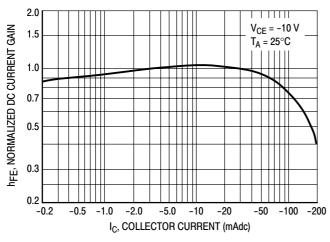


Figure 1. Normalized DC Current Gain

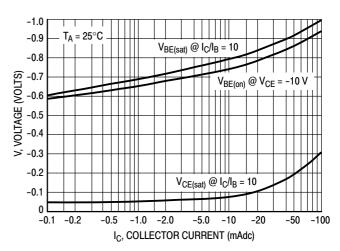


Figure 2. "Saturation" and "On" Voltages

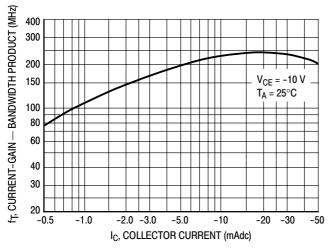


Figure 3. Current-Gain — Bandwidth Product

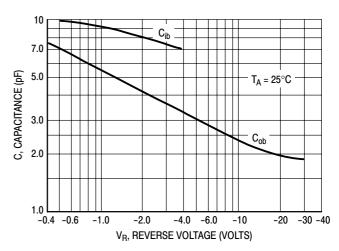


Figure 4. Capacitances

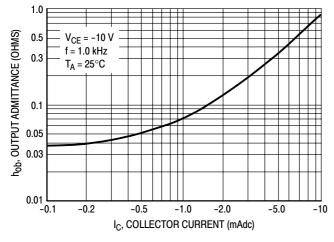


Figure 5. Output Admittance

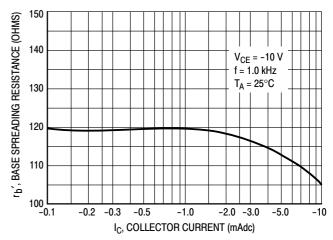
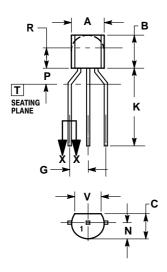


Figure 6. Base Spreading Resistance

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**





NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED.

 4. LEAD DIMENSION IS UNCONTROLLED IN P
 AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN MAX		
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
Р	1.50	4.00	
R	2.93		
V	3 43		

STYLE 17: PIN 1. COLLECTOR

BASE
 EMITTER

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